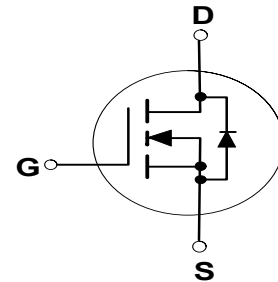




40V N-Channel PowerTrench MOSFET

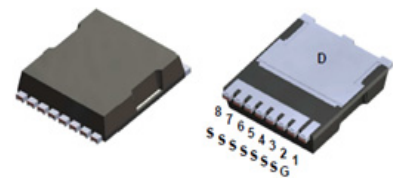
Application

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch



Features

- Typical  $R_{DS(on)} = 0.85\text{ m}\Omega$  at  $V_{GS} = 10\text{V}$ ,  $I_D = 80\text{ A}$
- Typical  $Q_g(tot) = 90\text{ nC}$  at  $V_{GS} = 10\text{V}$ ,  $I_D = 80\text{ A}$
- UIS Capability
- RoHS Compliant



MOSFET Maximum Ratings  $T_J = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Rated Values	Units
$V_{DSS}$	Drain-to-Source Voltage		40	V
$V_{GS}$	Gate-to-Source Voltage		$\pm 20$	V
$I_D$	Drain Current - Continuous ( $V_{GS}=10$ ) (Note 1)	$T_C = 25^\circ\text{C}$	260	A
	Pulsed Drain Current	$T_C = 25^\circ\text{C}$	See Figure 4	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 2)	316	mJ
$P_D$	Power Dissipation		300	W
	Derate Above $25^\circ\text{C}$		2.0	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature		-55 to + 175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	$^\circ\text{C}/\text{W}$

Notes:

- 1: Current is limited by bondwire configuration.
- 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.1\text{mH}$ ,  $I_{AS} = 79.5\text{A}$ ,  $V_{DD} = 40\text{V}$  during inductor charging and  $V_{DD} = 0\text{V}$  during time in avalanche.
- 3:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.



## 40V N-Channel PowerTrench MOSFET

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$B_{VDSS}$	Drain-to-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40	-	-	V
$I_{DSS}$	Drain-to-Source Leakage Current	$V_{DS} = 40\text{V}, T_J = 25^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{V}, T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	mA
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2.0	3.2	4.0	V
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}, T_J = 25^\circ\text{C}$	-	0.85	1.10	$\text{m}\Omega$
		$V_{GS} = 10\text{V}, T_J = 175^\circ\text{C}$ (Note 4)	-	1.64	1.86	$\text{m}\Omega$

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	7735	-	pF
$C_{oss}$	Output Capacitance		-	2160	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	129	-	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	2.5	-	$\Omega$
$Q_{g(ToT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	-	90	107	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V				
$Q_{gs}$	Gate-to-Source Gate Charge					
$Q_{gd}$	Gate-to-Drain "Miller" Charge		-	10	-	nC

**Switching Characteristics**

$t_{on}$	Turn-On Time	$V_{DD} = 20\text{V}, I_D = 80\text{A}, V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$	-	-	102	ns
$t_{d(on)}$	Turn-On Delay		-	33	-	ns
$t_r$	Rise Time		-	40	-	ns
$t_{d(off)}$	Turn-Off Delay		-	47	-	ns
$t_f$	Fall Time		-	23	-	ns
$t_{off}$	Turn-Off Time		-	-	91	ns

**Drain-Source Diode Characteristics**

$V_{SD}$	Source-to-Drain Diode Voltage	$I_{SD} = 80\text{A}, V_{GS} = 0\text{V}$	-	-	1.25	V
		$I_{SD} = 40\text{A}, V_{GS} = 0\text{V}$	-	-	1.2	V
$t_{rr}$	Reverse-Recovery Time	$I_F = 80\text{A}, di_{SD}/dt = 100\text{A}/\mu\text{s}$	-	91	107	ns
$Q_{rr}$	Reverse-Recovery Charge	$V_{DD} = 32\text{V}$	-	128	167	nC

**Note:**

4: The maximum value is specified by design at  $T_J = 175^\circ\text{C}$ . Product is not tested to this condition in production.



# 40V N-Channel PowerTrench MOSFET

## Typical Characteristics

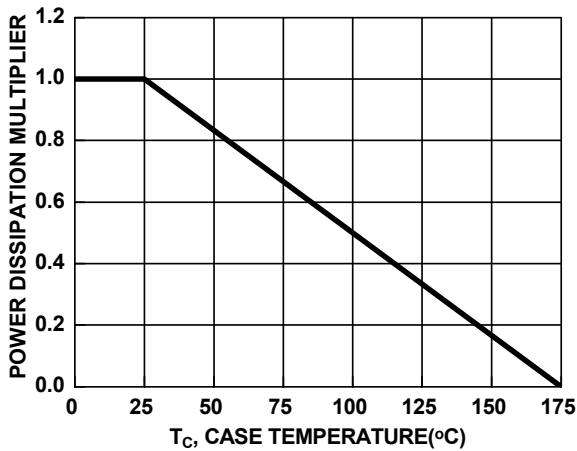


Figure 1. Normalized Power Dissipation vs. Case Temperature

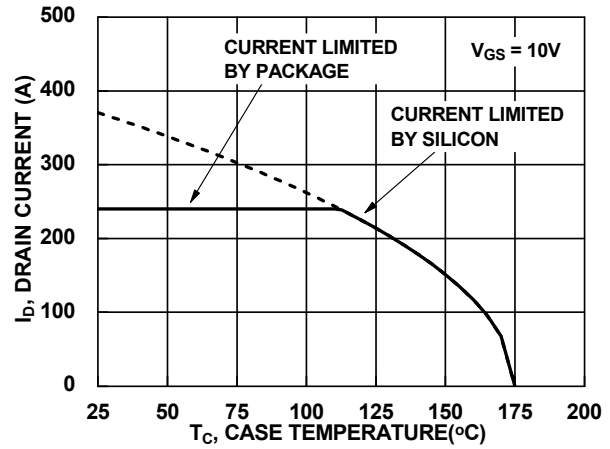


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

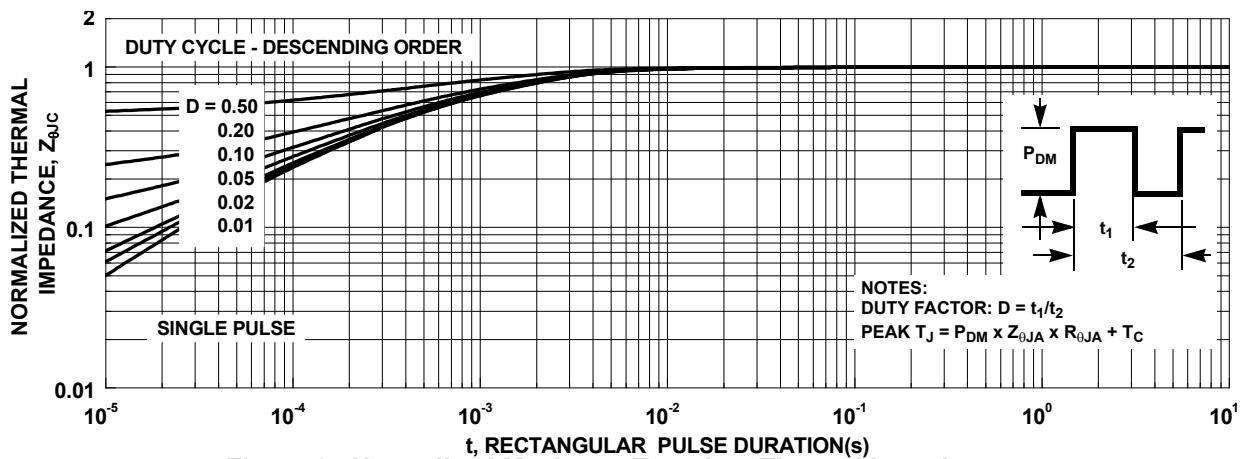


Figure 3. Normalized Maximum Transient Thermal Impedance

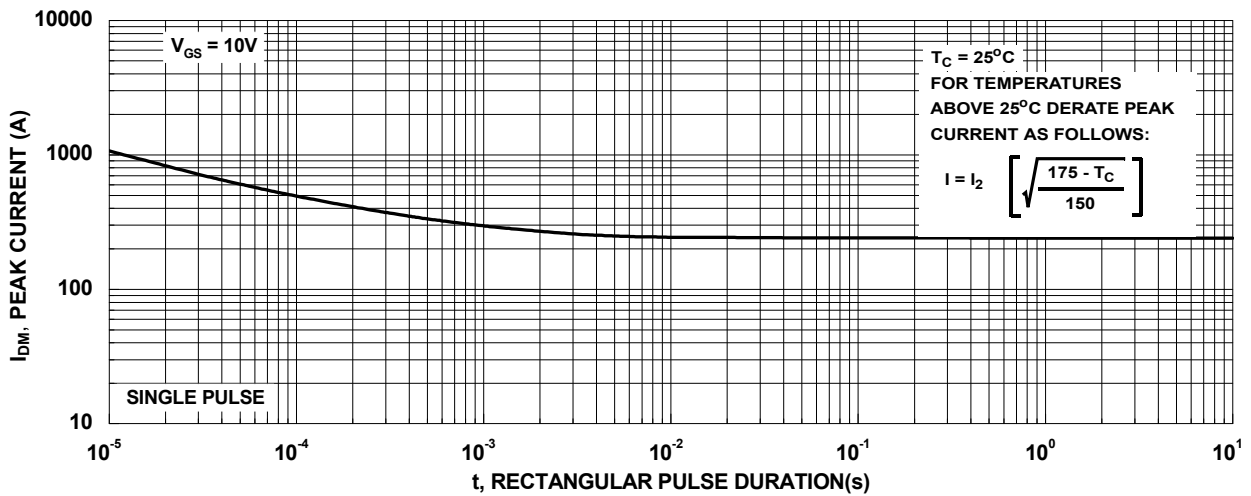


Figure 4. Peak Current Capability



# 40V N-Channel PowerTrench MOSFET

## Typical Characteristics

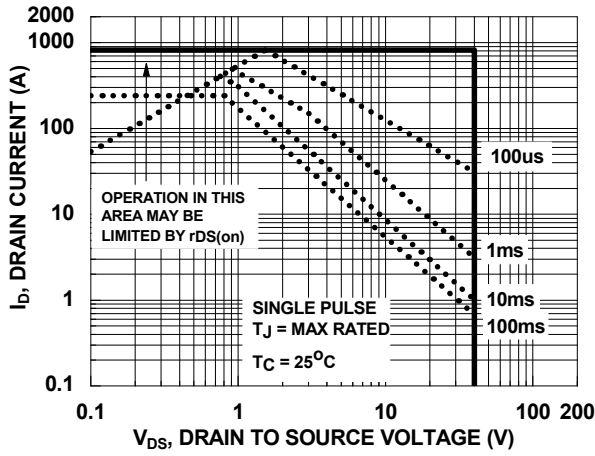
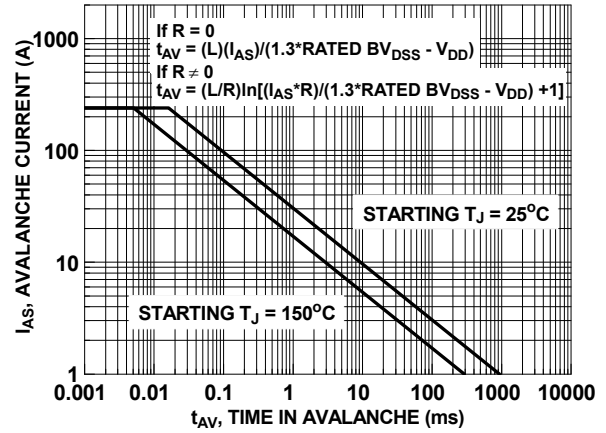


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515  
Figure 6. Unclamped Inductive Switching Capability

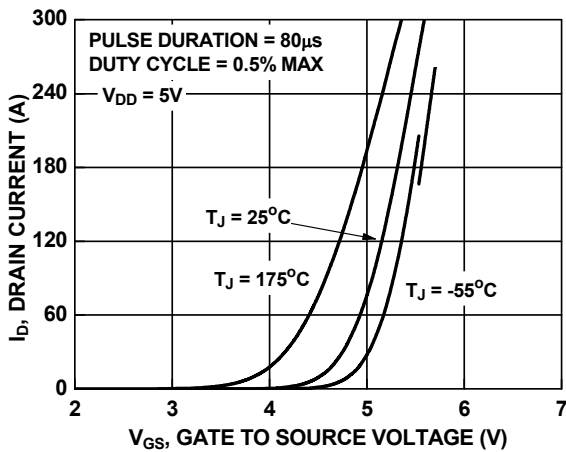


Figure 7. Transfer Characteristics

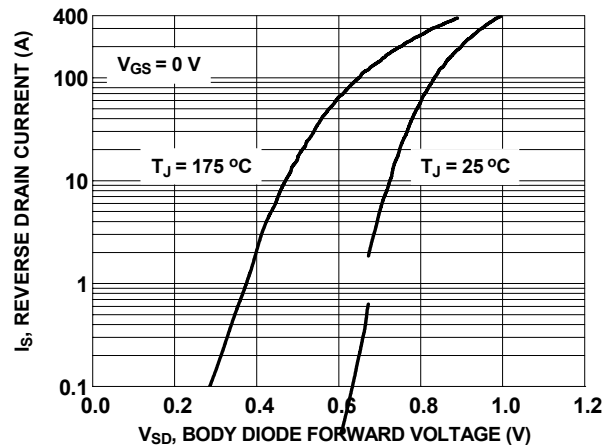


Figure 8. Forward Diode Characteristics

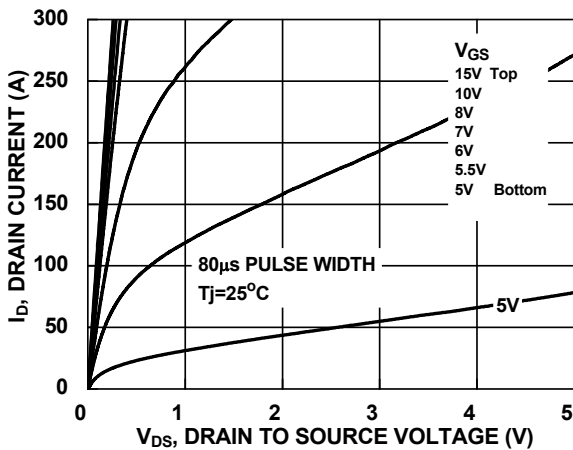


Figure 9. Saturation Characteristics

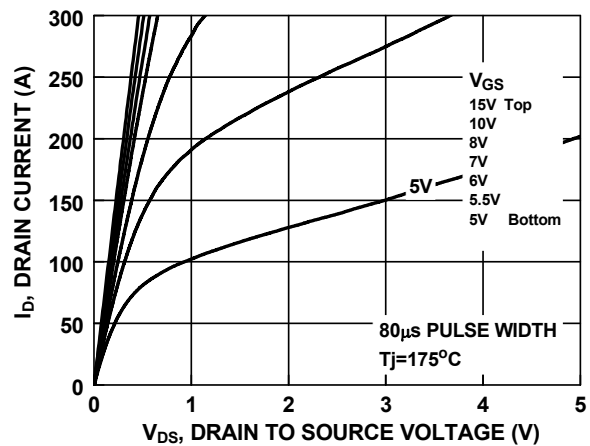


Figure 10. Saturation Characteristics



### 40V N-Channel PowerTrench MOSFET

#### Typical Characteristics

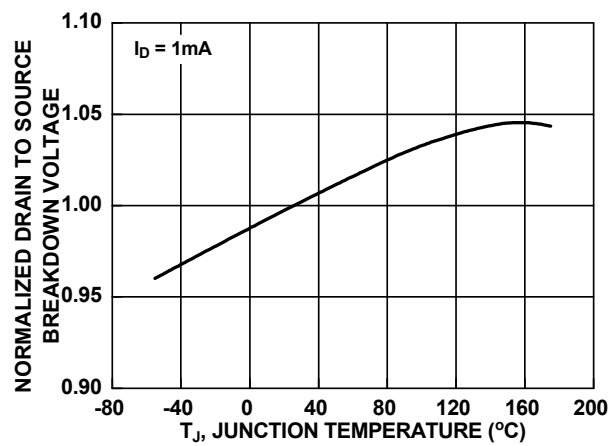
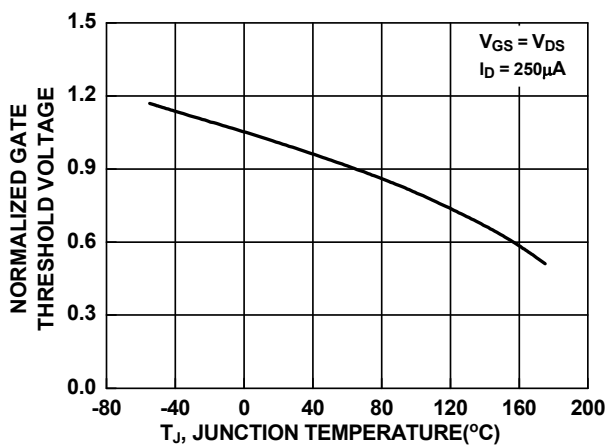
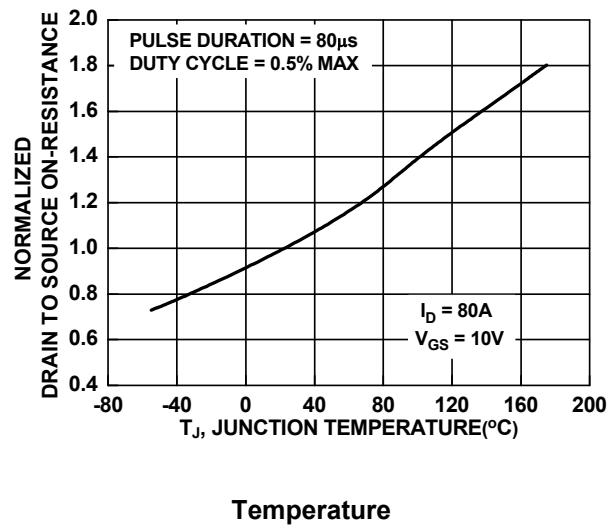
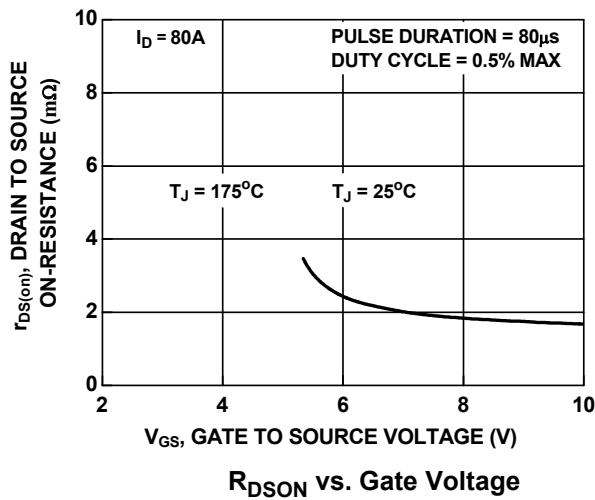


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

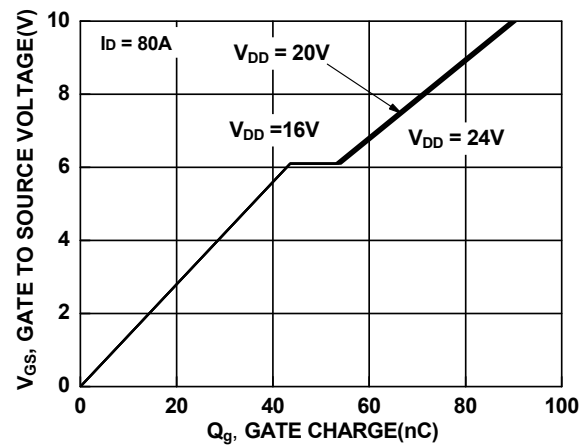
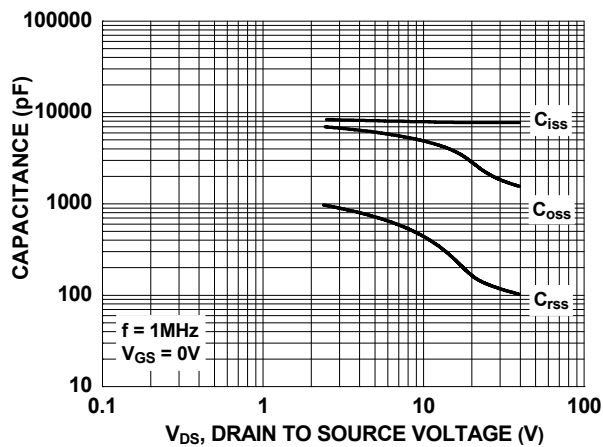


Figure 15. Capacitance vs. Drain to Source Voltage

Figure 16. Gate Charge vs. Gate to Source Voltage

